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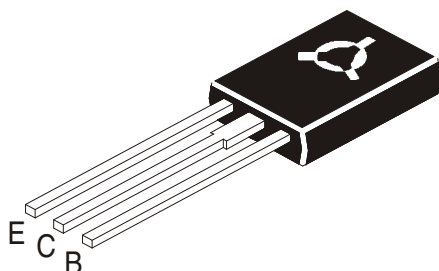
Please visit our website for pricing and availability at www.hestore.hu.

NPN EPITAXIAL SILICON POWER TRANSISTOR

MJE340

TO126

Plastic Package



For use in High Voltage General Purpose Applications

ABSOLUTE MAXIMUM RATINGS

DESCRIPTION	SYMBOL	VALUE	UNIT
Collector Emitter Voltage	V_{CEO}	300	V
Collector Base Voltage	V_{CBO}	300	V
Emitter Base Voltage	V_{EBO}	3.0	V
Collector Current Continuous	I_C	500	mA
Power Dissipation @ $T_a=25^{\circ}\text{C}$ Derate above 25°C	P_D	1.25 10	W mW/ $^{\circ}\text{C}$
Power Dissipation @ $T_c=25^{\circ}\text{C}$ Derate above 25°C	P_D	20 0.16	W W/ $^{\circ}\text{C}$
Operating And Storage Junction Temperature Range	T_j, T_{stg}	- 65 to +150	$^{\circ}\text{C}$

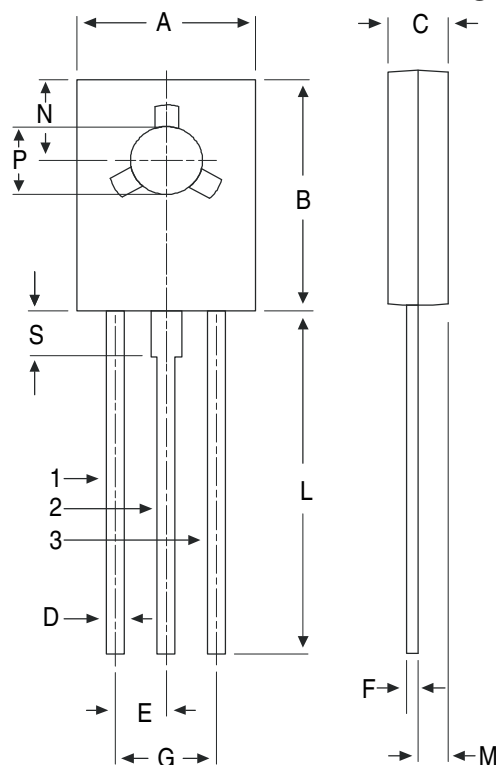
THERMAL CHARACTERISTICS

Junction to Ambient in free air	$R_{th(j-a)}$	100	$^{\circ}\text{C/W}$
Junction to Case	$R_{th(j-c)}$	6.25	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_c=25^{\circ}\text{C}$ unless specified otherwise)

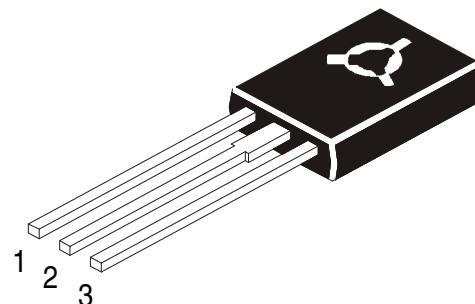
DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Collector Emitter Sustaining Voltage	$*V_{CEO(sus)}$	$I_C=1\text{mA}, I_B=0$	300		V
Collector Cut Off Current	I_{CBO}	$V_{CB}=300\text{V}, I_E=0$		100	μA
Emitter Cut Off Current	I_{EBO}	$V_{EB}=3\text{V}, I_C=0$		100	μA
DC Current Gain	h_{FE}	$I_C=50\text{mA}, V_{CE}=10\text{V}$	30	240	

TO-126 (SOT-32) Plastic Package



DIM	MIN	MAX
A	7.4	7.8
B	10.5	10.8
C	2.4	2.7
D	0.7	0.9
E	2.25 TYP.	
F	0.49	0.75
G	4.5 TYP.	
L	15.7 TYP.	
M	1.27 TYP.	
N	3.75 TYP.	
P	3.0	3.2
S	2.5 TYP.	

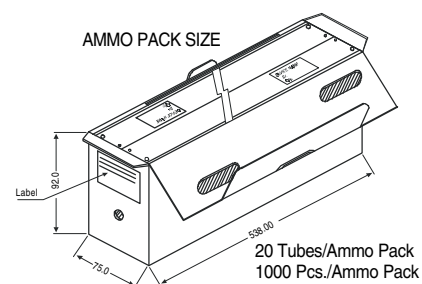
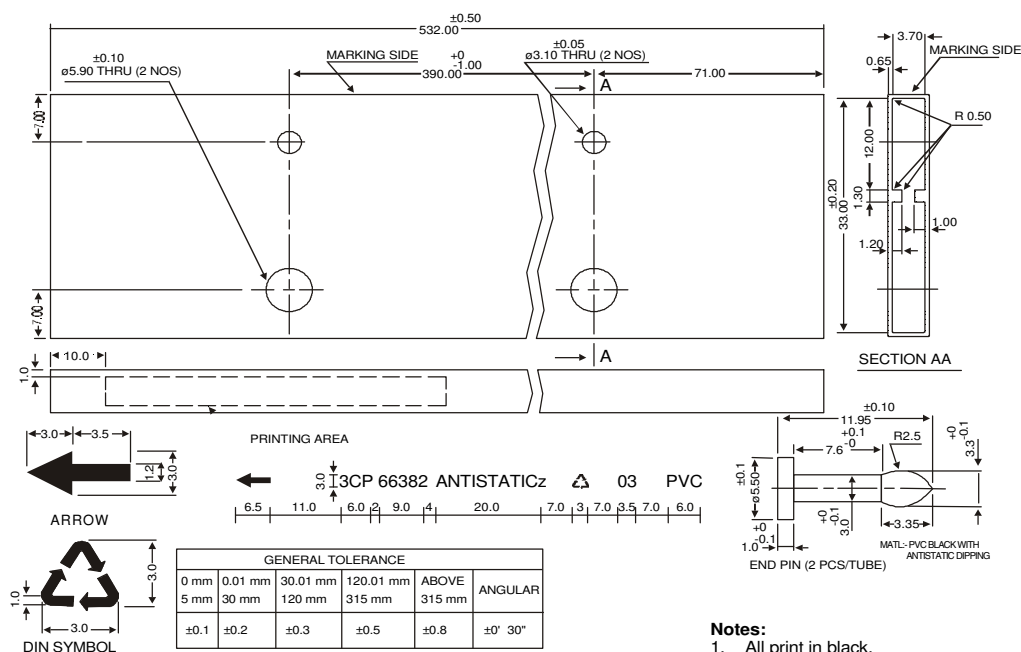
All dimensions in mm.



Pin Configuration

1. Emitter
2. Collector
3. Base

TO-126 TUBE PACKING



Packing Details

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/ Qty	Size	Qty	Size	Qty	Gr Wt
TO-126 Bulk	500 pcs/polybag	340 gm/500 pcs	3" x 7.5" x 7.5"	2K	17" x 15" x 13.5"	32K	31 kgs
TO-126 Tube	50 pcs/tube	73 gm/50 pcs	3" x 3.7" x 21.5"	1K	19" x 19" x 19"	10K	15 kgs

Disclaimer

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